

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1-2. (Canceled)

3. (Currently amended) ~~The semiconductor light emitting device according to claim 2,~~

A semiconductor light emitting device comprising:

a nitride-based semiconductor layer including an emission layer; and

a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein

said dielectric film contains a nitride on the side of the interface between said dielectric film and said nitride-based semiconductor layer while containing an oxide on the side opposite to said nitride-based semiconductor layer, and further wherein said dielectric film successively includes a nitride film and an oxide film as said nitride and said oxide;

wherein

said dielectric film further includes a compound film containing nitrogen and oxygen between said nitride film and said oxide film.

4. (Original) The semiconductor light emitting device according to claim 3, wherein

said compound film has such a graded composition that the content of nitrogen gradually reduces and the content of oxygen gradually increases from the side of the interface between said compound film and said nitride film toward the side of the interface between said compound film and said oxide film.

5. (Currently amended) The semiconductor light emitting device according to ~~claim 2~~
claim 3, wherein

said nitride film is a silicon nitride film or a titanium nitride film, and said oxide film is a
silicon oxide film or a titanium oxide film.

6. (Currently amended) ~~The semiconductor light emitting device according to claim 1,~~
A semiconductor light emitting device comprising:
a nitride-based semiconductor layer including an emission layer; and
a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein
said dielectric film contains a nitride on the side of the interface between said dielectric
film and said nitride-based semiconductor layer while containing an oxide on the side opposite to
said nitride-based semiconductor layer;

wherein

said dielectric film includes a compound film containing nitrogen and oxygen as said
nitride and said oxide, and said compound film has such a graded composition that the content of
nitrogen gradually reduces and the content of oxygen gradually increases from the side of the
interface between said compound film and said nitride-based semiconductor layer toward the
opposite side.

7. (Original) The semiconductor light emitting device according to claim 6, wherein said
compound film is a compound film containing silicon or titanium and containing nitrogen and
oxygen.

8. (Previously presented) A semiconductor light emitting device comprising:
a nitride-based semiconductor layer including an emission layer; and
a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein
said dielectric film contains a compound containing nitrogen and oxygen on the side of
the interface between said dielectric film and said nitride-based semiconductor layer while
containing an oxide on the side opposite to said nitride-based semiconductor layer.

9. (Original) The semiconductor light emitting device according to claim 8, wherein
said dielectric film includes a compound film as said compound and includes an oxide
film as said oxide, while said compound film has such a graded composition that the content of
nitrogen gradually reduces and the content of oxygen gradually increases from the side of the
interface between said compound film and said nitride-based semiconductor layer toward the
opposite side.

10. (Original) The semiconductor light emitting device according to claim 9, wherein
said compound film is a compound film containing silicon or titanium and containing
nitrogen and oxygen, and said oxide film is a silicon oxide film or a titanium oxide film.

11. (Previously presented) A semiconductor light emitting device comprising:
a nitride-based semiconductor layer including an emission layer; and
a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein
said dielectric film contains a nitride on the side of the interface between said dielectric
film and said nitride-based semiconductor layer while containing a compound containing
nitrogen and oxygen on the side opposite to said nitride-based semiconductor layer.

12. (Previously presented) The semiconductor light emitting device according to claim 11, wherein

said dielectric film includes a nitride film as said nitride and includes a compound film as said compound, and said compound film has such a graded composition that the content of nitrogen gradually reduces and the content of oxygen gradually increases from the side of the interface between said compound film and said nitride film toward the opposite side.

13. (Original) The semiconductor light emitting device according to claim 12, wherein said nitride film is a silicon nitride film or a titanium nitride film, and said compound film is a compound film containing silicon or titanium and containing nitrogen and oxygen.

14. (Currently amended) ~~The semiconductor light emitting device according to claim 1,~~
A semiconductor light emitting device comprising:
a nitride-based semiconductor layer including an emission layer; and
a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein
said dielectric film contains a nitride on the side of the interface between said dielectric
film and said nitride-based semiconductor layer while containing an oxide on the side opposite to
said nitride-based semiconductor layer;

wherein

said nitride-based semiconductor layer further includes a cladding layer formed on said emission layer, said cladding layer has a flat portion and a ridge portion located on said flat portion, and said dielectric film is formed on said flat portion of said cladding layer and the side surface of said ridge portion.

15. (Original) The semiconductor light emitting device according to claim 14, wherein the side surface of said ridge portion is irregularized, and said dielectric film is formed on said flat portion of said cladding layer and the side surface of said ridge portion.

16. (Currently amended) ~~The semiconductor light emitting device according to claim 1,~~
A semiconductor light emitting device comprising:
a nitride-based semiconductor layer including an emission layer; and
a dielectric film formed on the surface of said nitride-based semiconductor layer, wherein
said dielectric film contains a nitride on the side of the interface between said dielectric
film and said nitride-based semiconductor layer while containing an oxide on the side opposite to
said nitride-based semiconductor layer;

wherein

said nitride-based semiconductor layer further includes a first conductivity type semiconductor layer provided under said emission layer and a second conductivity type semiconductor layer provided on said emission layer, a partial region of said nitride-based semiconductor layer is removed to partially expose said first conductivity type semiconductor layer, a first electrode is formed on said exposed region of said first conductivity type semiconductor layer, a second electrode is formed on said second conductivity type semiconductor layer, and said dielectric film is formed on the surface of said nitride-based semiconductor layer between said first electrode and said second electrode.

17. (Previously presented) A semiconductor light emitting device comprising:
an emission layer composed of a nitride-based semiconductor;
a cladding layer formed on said emission layer and composed of a nitride-based semiconductor having a flat portion and a ridge portion located on said flat portion; the side surface of said ridge portion of said cladding layer being irregularized, and
a dielectric film formed on said flat portion of said cladding layer and the side surface of said ridge portion.

18. (Previously presented) The semiconductor light emitting device according to claim 17, wherein said dielectric film contains a nitride on the side of the interface between said dielectric film and said nitride-based semiconductor layer while containing an oxide on the side opposite to said nitride-based semiconductor layer.

19. (Previously presented) The semiconductor light emitting device according to claim 17, wherein said dielectric film contains a compound containing nitrogen and oxygen on the side of the interface between said dielectric film and said nitride-based semiconductor layer while containing an oxide on the side opposite to said nitride-based semiconductor layer.

20. (Previously presented) The semiconductor light emitting device according to claim 17, wherein

said dielectric film contains a nitride on the side of the interface between said dielectric film and said nitride-based semiconductor layer while containing a compound containing nitrogen and oxygen on the side opposite to said nitride-based semiconductor layer.